

STP16NF06 STP16NF06FP

N-channel 60V - 0.08Ω - 16A - TO-220/TO-220FP STripFET™ II Power MOSFET

General features

Туре	V _{DSS}	R _{DS(on)}	I _D
STP16NF06	60V	<0.1Ω	16A
STP16NF06FP	60V	<0.1Ω	11A

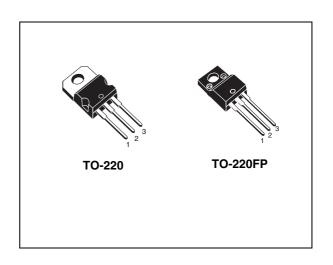
- Exceptional dv/dt capability
- Low gate charge at 100°C
- Application oriented characterization

Description

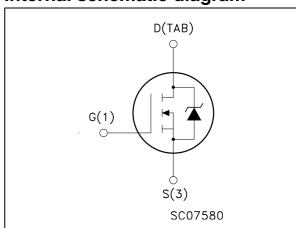
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature SizeTM" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

Applications

■ Switching application



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STP16NF06	TP16NF06 P16NF06 TO-220		Tube
STP16NF06FP	P16NF06	TO-220FP	Tube

Contents

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2	Electrical characteristics
	2.1 Electrical characteristics (curves)
3	Test circuit
4	Package mechanical data
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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Va	lue	Unit
		TO-220	TO-220FP	
V _{DS}	Drain-source voltage (V _{GS} = 0)	6	0	V
V _{GS}	Gate- source voltage	±	20	V
I _D	Drain current (continuous) at T _C = 25°C	16	11 ⁽¹⁾	Α
I _D	Drain current (continuous) at T _C = 100°C	11	7.5 ⁽¹⁾	Α
I _{DM} ⁽²⁾	Drain current (pulsed)	64	44 ⁽¹⁾	Α
P _{tot}	Total dissipation at T _C = 25°C	45	25	W
	Derating factor	0.3	0.17	W/°C
dv/dt (3)	Peak diode recovery voltage slope	2	V/ns	
E _{AS} (4)	Single pulse avalanche energy	130		mJ
I _{AR}	Avalanche current, repetitive or not- repetitive	1	6	Α
V _{ISO}	Insulation withstand voltage (DC)		2500	V
T _{stg}	Storage temperature	55 to 175		°C
Tj	Max. operating junction temperature	-55 to 175		C

- 1. Current limited by package's thermal resistance
- 2. Pulse width limited by safe operating area.
- 3. $I_{SD} \leq 16A$, di/dt $\leq 200A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $Tj \leq T_{JMAX}$
- 4. Starting $T_i = 25$ °C, $I_D = 8A$, $V_{DD} = 30V$

Table 2. Thermal data

	TO-220 TO-220FP					
Rthj-case	Thermal resistance junction-case max 3.33 6					
Rthj-amb	Thermal resistance junction-ambient max	62	°C/W			
TJ	Maximum lead temperature for soldering purpose	30	°C			

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2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	60			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V_{DS} = max ratings V_{DS} = max ratings, T_{C} = 125°C			1 10	μ Α μ Α
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 20V			±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2		4	V
R _{DS(on)}	Static drain-source on resistance	$V_{GS} = 10V, I_D = 8A$		0.08	0.1	Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
9 _{fs} ⁽¹⁾	Forward transconductance	V _{DS} = 15V, I _D = 8A		6.5		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1MHz,$ $V_{GS} = 0$		315 70 30		pF pF pF
t _{d(on)} t _r t _{d(off)} t _f	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD} = 30V, I_{D} = 8A R_{G} = 4.7 Ω V_{GS} = 10V (see <i>Figure 15</i>)		7 18 17 6		ns ns ns
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 48V$, $I_D = 16A$, $V_{GS} = 10V$ (see <i>Figure 16</i>)		10 3.5 3.5	13	nC nC nC

^{1.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%.

Table 5. Source drain diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD}	Source-drain current Source-drain current (pulsed)				16 64	A A
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = 16A, V _{GS} = 0			1.3	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 15A$, $di/dt = 100A/\mu s$, $V_{DD} = 30V$, $T_j = 150^{\circ}C$ (see <i>Figure 17</i>)		50 88 3.5		ns nC A

- 1. Pulse width limited by safe operating area.
- 2. Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220

Figure 2. Thermal impedance for TO-220

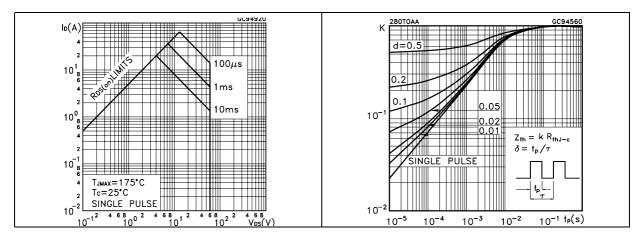


Figure 3. Safe operating area for TO-220FP

Figure 4. Thermal impedance for TO-220FP

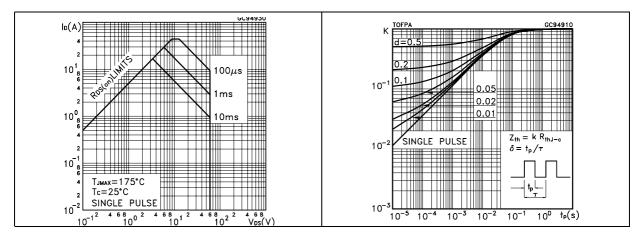
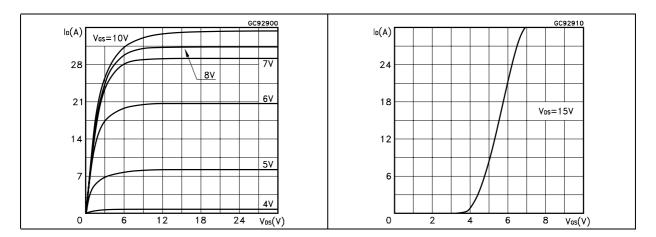


Figure 5. Output characteristics

Figure 6. Transfer characteristics



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Figure 7. Transconductance

Figure 8. Static drain-source on resistance

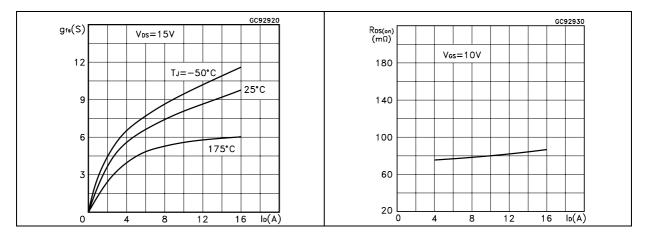


Figure 9. Gate charge vs. gate-source voltage Figure 10. Capacitance variations

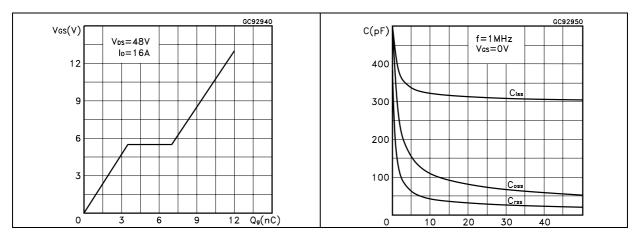


Figure 11. Normalized gate threshold voltage Figure 12. Normalized on resistance vs. vs. temperature temperature

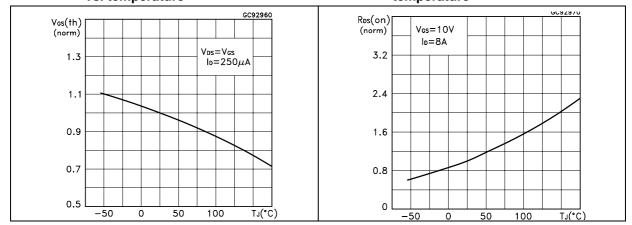
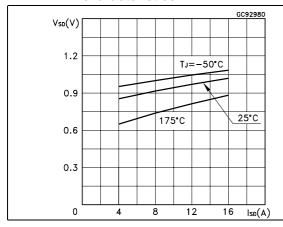
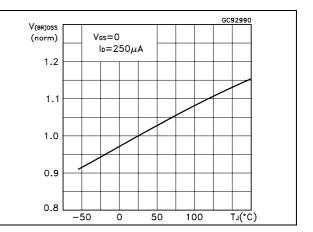


Figure 13. Source-drain diode forward characteristics

Figure 14. Normalized \mathbf{B}_{VDSS} vs. temperature





3 Test circuit

Figure 15. Switching times test circuit for resistive load

Figure 16. Gate charge test circuit

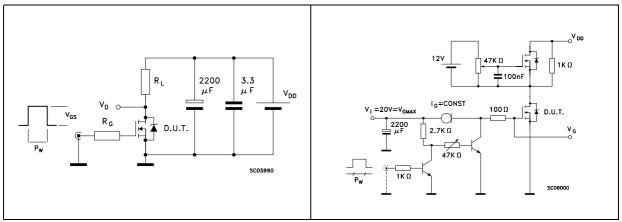


Figure 17. Test circuit for inductive load switching and diode recovery times

Figure 18. Unclamped Inductive load test circuit

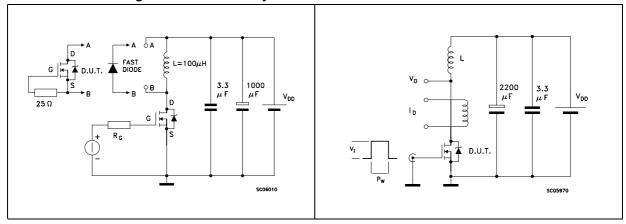
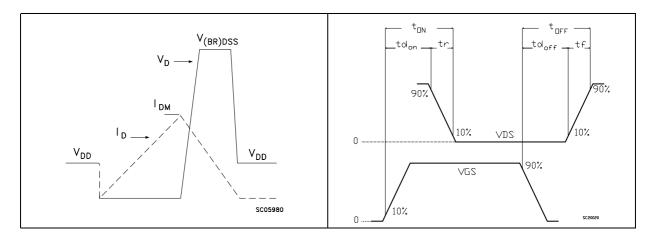


Figure 19. Unclamped inductive waveform

Figure 20. Switching time waveform



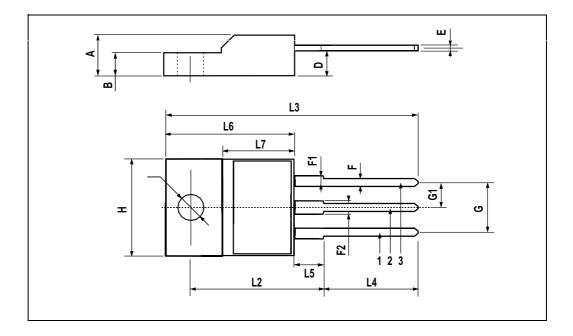
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4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-220FP MECHANICAL DATA

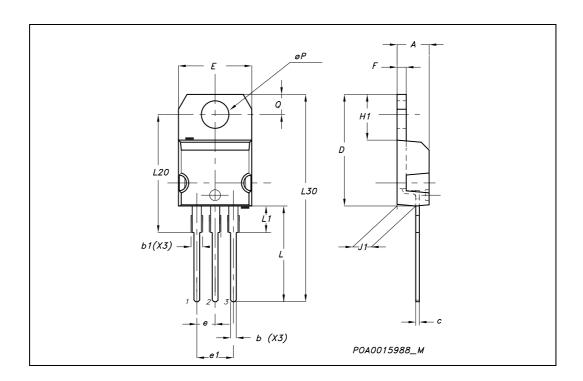
DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.4		4.6	0.173		0.181
В	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
Н	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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TO-220 MECHANICAL DATA

DIM.	mm. inch			inch		
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
С	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øΡ	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



5 Revision history

Table 6. Revision history

Date	Revision	Changes
09-Sep-2004	4	Preliminary version
28-Jun-2005	5	Complete version
21-Jul-2005	6	ECOPACK label inserted
09-Aug-2006	7	New template, no content change
20-Feb-2007	8	Typo mistake on page 1

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